

Adalberto Balzarotti

List of Publications by Year in descending order

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papers

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191
docs citations

191
times ranked

1859
citing authors

#	ARTICLE	IF	CITATIONS
1	Model of the local structure of random ternary alloys: Experiment versus theory. Physical Review B, 1985, 31, 7526-7539.	1.1	204
2	Local structure of ternary semiconducting random solid solutions: Extended x-ray-absorption fine structure of $\text{Cd}_{1-x}\text{Mn}_x\text{Te}$. Physical Review B, 1984, 30, 2295-2298.	1.1	197
3	Electronic Structure of Aluminium Oxide as Determined by X-Ray Photoemission. Physica Status Solidi (B): Basic Research, 1976, 76, 689-694.	0.7	96
4	Electronic properties of the III-VI layer compounds GaS, GaSe and InSe. I: Band structure. Societa Italiana Di Fisica Nuovo Cimento B-General Physics, Relativity Astronomy and Mathematical Physics and Methods, 1979, 51, 154-180.	0.2	93
5	EXAFS measurements on Fe-B metallic glasses: Asymmetry of the radial distribution function. Solid State Communications, 1981, 37, 921-923.	0.9	89
6	Palladium clusters on graphite: Evidence of resonant hybrid states in the valence and conduction bands. Physical Review B, 1990, 41, 5685-5695.	1.1	83
7	Growth of Ge-Si(111) epitaxial layers: intermixing, strain relaxation and island formation. Surface Science, 1998, 406, 254-263.	0.8	76
8	Tracing the two- to three-dimensional transition in the InAs/GaAs(001) heteroepitaxial growth. Physical Review B, 2003, 67, .	1.1	69
9	EXAFS of $\text{Cd}_{1-x}\text{Zn}_x\text{Te}$: A test of the random distribution in zincblende ternary alloys. Solid State Communications, 1985, 53, 509-512.	0.9	68
10	Valence charge fluctuations in $\text{YBa}_2\text{Cu}_3\text{O}_{7-\delta}$ from core-level spectroscopies. Physical Review B, 1988, 38, 6461-6469.	1.1	65
11	Self-ordering of Ge islands on step-bunched Si(111) surfaces. Applied Physics Letters, 2003, 83, 4002-4004.	1.5	63
12	Crystallographic structure of ternary semiconducting alloys. Solid State Communications, 1985, 55, 413-417.	0.9	58
13	Bremsstrahlung-isochromat-spectroscopy and x-ray-photoelectron-spectroscopy investigation of the electronic structure of $\text{I}^2\text{-FeSi}_2$ and the Fe/Si(111) interface. Physical Review B, 1990, 42, 5871-5874.	1.1	55
14	Topographic and spectroscopic analysis of ethylene adsorption on Si(111) $\sqrt{7}\times\sqrt{7}$ by STM and STS. Physical Review B, 1993, 48, 17892-17896.	1.1	53
15	Core Transitions from the Al 2p Level in Amorphous and Crystalline Al_2O_3 . Physica Status Solidi (B): Basic Research, 1974, 63, 77-87.	0.7	51
16	Step erosion during nucleation of InAs-GaAs(001) quantum dots. Applied Physics Letters, 2005, 86, 241913.	1.5	50
17	Apparent critical thickness versus temperature for InAs quantum dot growth on GaAs(001). Applied Physics Letters, 2006, 88, 161903.	1.5	49
18	Random distribution and miscibility of $\text{Cd}_{1-x}\text{Zn}_x\text{Te}$ alloy from exafs. Journal of Crystal Growth, 1985, 72, 205-209.	0.7	48

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19	Electronic relaxation effects on x-ray spectra of titanium and transition-metal carbides and nitrides. <i>Physical Review B</i> , 1982, 25, 6349-6366.	1.1	45
20	EXAFS investigation of amorphous-to-crystal transition in Ge. <i>Solid State Communications</i> , 1981, 37, 413-416.	0.9	44
21	EXAFS of the superconducting oxide $\text{BaPb}_{1-x}\text{Bi}_x\text{O}_3$. <i>Solid State Communications</i> , 1984, 49, 887-890.	0.9	42
22	Shaping Ge Islands on Si(001) Surfaces with Misorientation Angle. <i>Physical Review Letters</i> , 2010, 104, 036104.	2.9	42
23	van der Waals Heteroepitaxy of Germanene Islands on Graphite. <i>Journal of Physical Chemistry Letters</i> , 2016, 7, 3246-3251.	2.1	42
24	Electronic properties of the III-VI layer compounds GaS, GaSe and InSe. II: Photoemission. <i>Societa Italiana Di Fisica Nuovo Cimento B-General Physics, Relativity Astronomy and Mathematical Physics and Methods</i> , 1979, 51, 181-197.	0.2	41
25	Kinetic aspects of the morphology of self-assembled InAs quantum dots on GaAs(001). <i>Applied Physics Letters</i> , 2001, 78, 320-322.	1.5	40
26	Atomic bonding and thermodynamic properties of pseudo-binary semiconducting alloys. <i>Journal of Physics C: Solid State Physics</i> , 1987, 20, 2853-2884.	1.5	39
27	Electronic energy levels of Al_2O_3 from L-edge photoabsorption of aluminum and small-cluster CNDO calculations. <i>Physical Review B</i> , 1984, 29, 5903-5908.	1.1	38
28	Real-time scanning tunneling microscopy observation of the evolution of Ge quantum dots on nanopatterned Si(001) surfaces. <i>Physical Review B</i> , 2004, 69, .	1.1	38
29	Excitonic effect at the direct absorption edges of GaSe. <i>Solid State Communications</i> , 1972, 10, 421-425.	0.9	37
30	Electronic correlations in $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$ from Auger spectroscopy. <i>Physical Review B</i> , 1987, 36, 8285-8287.	1.1	37
31	How kinetics drives the two- to three-dimensional transition in semiconductor strained heterostructures: The case of InAs/GaAs(001). <i>Applied Physics Letters</i> , 2006, 89, 041904.	1.5	37
32	Early stage of Ge growth on Si(001) vicinal surfaces with an 8° miscut along [110]. <i>Physical Review B</i> , 2007, 75, .	1.1	36
33	Evidence of hydrogen-induced levels in Pd from X-ray photoemission. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 1975, 55, 309-310.	0.9	35
34	Analysis of Critical Points of Graphite from Temperature-Modulated Reflectance. <i>Physical Review Letters</i> , 1968, 20, 9-11.	2.9	34
35	Thermodynamic properties of ternary semiconducting alloys. <i>European Physical Journal B</i> , 1986, 62, 153-161.	0.6	34
36	Structural and electronic properties of Fe and TiFe from extended and near-edge x-ray-absorption structure. <i>Physical Review B</i> , 1983, 27, 4712-4721.	1.1	32

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37	Temperature dependence of the size distribution function of InAs quantum dots on GaAs(001). <i>Physical Review B</i> , 2010, 81, .	1.1	32
38	Temperature-modulated reflectance of GaSe at the ground state exciton line. <i>Physica Status Solidi (B): Basic Research</i> , 1971, 44, 713-716.	0.7	31
39	Self-assembly of InAs and Si/Ge quantum dots on structured surfaces. <i>Journal of Physics Condensed Matter</i> , 2004, 16, S1503-S1534.	0.7	31
40	InAs/GaAs(001) epitaxy: kinetic effects in the two-dimensional to three-dimensional transition. <i>Journal of Physics Condensed Matter</i> , 2007, 19, 225006.	0.7	31
41	Electroreflectance and band structure of gallium selenide. <i>Journal of Physics C: Solid State Physics</i> , 1971, 4, L273-L278.	1.5	29
42	K-edge absorption of titanium in the perovskites SrTiO ₃ , BaTiO ₃ and TiO ₂ . <i>Solid State Communications</i> , 1980, 35, 145-149.	0.9	29
43	Morphological instabilities of the InAs/GaAs(001) interface and their effect on the self-assembling of InAs quantum-dot arrays. <i>Applied Physics Letters</i> , 2002, 81, 2270-2272.	1.5	29
44	Sudden nucleation versus scale invariance of InAs quantum dots on GaAs. <i>Physical Review B</i> , 2007, 75, .	1.1	29
45	Core excitons in corundum. <i>Solid State Communications</i> , 1982, 44, 275-278.	0.9	28
46	Growth of ultrahigh-density quantum-confined germanium dots on SiO ₂ thin films. <i>Applied Physics Letters</i> , 2006, 89, 063122.	1.5	28
47	Reflection high energy electron diffraction observation of surface mass transport at the two- to three-dimensional growth transition of InAs on GaAs(001). <i>Applied Physics Letters</i> , 2005, 87, 252101.	1.5	27
48	Iron disilicide growth on Si(111): a scanning tunneling microscopy investigation. <i>Surface Science</i> , 1993, 284, 257-262.	0.8	25
49	Kramers-Krönig analysis of modulated reflectance data investigation of errors. <i>Applied Optics</i> , 1975, 14, 2412.	2.1	24
50	Surface versus bulk contributions from reflectance anisotropy and electron energy loss spectra of the GaAs(001) $\sqrt{4 \times 4}$ surface. <i>Physical Review B</i> , 2003, 68, .	1.1	22
51	Role of the density of conduction states on the L _{2,3} absorption spectrum of aluminum. <i>Physical Review B</i> , 1974, 9, 5003-5007.	1.1	21
52	Effect of relaxation of the second-nearest neighbors on the thermodynamic properties of semiconducting alloys: Application to GaAs _{1-y} Sb _y . <i>Physical Review B</i> , 1989, 39, 5987-5997.	1.1	21
53	Band structure and electronic properties of FeSi and FeSi_2 . <i>Journal of Applied Physics</i> , 1994, 76, 2837-2840.	1.1	21
54	GeSi intermixing in Ge nanostructures on Si(111): An XAFS versus STM study. <i>Physical Review B</i> , 2007, 75, .	1.1	20

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55	XPS line shape asymmetry in the Pd-H system: The role of the electron screening. <i>Solid State Communications</i> , 1977, 21, 201-204.	0.9	19
56	Controlling the quantum dot nucleation site. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2003, 101, 77-88.	1.7	19
57	Surface states at the GaAs(001)2 \times 4 surface. <i>Physical Review B</i> , 2004, 69, .	1.1	19
58	X-ray photoelectron spectrum and two-dimensional band structure of InSe. <i>Solid State Communications</i> , 1977, 24, 327-329.	0.9	18
59	EXAFS of Cd $_{1-x}$ Zn $_x$ Te: A test of the random distribution in zincblende ternary alloys. <i>Festkörpersprobleme</i> , 1985, , 689-698.	0.7	18
60	Scaling law and dynamical exponent in the Volmer-Weber growth mode: silver on GaAs(001)2 \times 4. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2000, 69-70, 243-246.	1.7	18
61	EXAFS study of the [BaCuO $_2$] $_2$ /[(Ca,Sr)CuO $_2$] $_n$ artificial superconducting superlattices. <i>Physica C: Superconductivity and Its Applications</i> , 2000, 334, 64-76.	0.6	18
62	Short-range order and clustering in Ga $_{1-x}$ Al $_x$ As and its heterostructures. <i>Solid State Communications</i> , 1985, 56, 471-473.	0.9	17
63	Lattice distortions around atomic substitutions in II-VI alloys. <i>Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics</i> , 1987, 146, 150-175.	0.9	17
64	Energy loss study of the electronic structure of YBa $_2$ Cu $_3$ O $_{7-\delta}$ high T $_c$ superconductor. <i>Solid State Communications</i> , 1988, 68, 381-386.	0.9	17
65	Electronic structure of epitaxial $\hat{1}^2$ -FeSi $_2$ on Si(111). <i>Surface Science</i> , 1991, 251-252, 175-179.	0.8	17
66	Well-ordered (100) InAs surfaces using wet chemical treatments. <i>Surface Science</i> , 2004, 570, 237-244.	0.8	17
67	Influence of patterning on the nucleation of Ge islands on Si and SiO $_2$ surfaces. <i>Surface Science</i> , 2007, 601, 2778-2782.	0.8	17
68	Step-step interaction on vicinal Si(001) surfaces studied by scanning tunneling microscopy. <i>Physical Review B</i> , 2009, 80, .	1.1	17
69	Heteroepitaxy of Ge on singular and vicinal Si surfaces: elastic field symmetry and nanostructure growth. <i>Journal of Physics Condensed Matter</i> , 2015, 27, 253001.	0.7	17
70	High-Resolution Reflection Spectra of Alkali Halides in the Far Ultraviolet. <i>Physical Review B</i> , 1973, 7, 1541-1549.	1.1	16
71	Role of patterning in islands nucleation on semiconductor surfaces. <i>Comptes Rendus Physique</i> , 2006, 7, 1046-1072.	0.3	16
72	Intermixing and buried interfacial structure in strained Ge/Si(105) facets. <i>Physical Review B</i> , 2013, 88, .	1.1	16

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73	Core-level changes induced by oxygen in YBa ₂ Cu ₃ O _{7-δ} . Physical Review B, 1991, 43, 351-358.	1.1	15
74	Breaking Elastic Field Symmetry with Substrate Vicinality. Physical Review Letters, 2011, 106, 055503.	2.9	15
75	Thermoreflectance spectrum of silicon. Solid State Communications, 1968, 6, 815-820.	0.9	14
76	Polarization Effects in the Electroreflectance of Bismuth Telluride at Oblique Incidence. Physical Review B, 1971, 3, 1159-1167.	1.1	14
77	Ripple-to-dome transition: The growth evolution of Ge on vicinal Si(1 1 10) surface. Physical Review B, 2010, 82, .	1.1	14
78	Orientalional phase diagram of the epitaxially strained Si(001): Evidence of a singular (105) face. Physical Review B, 2012, 85, .	1.1	14
79	The Unexpected Role of Arsenic in Driving the Selective Growth of InAs Quantum Dots on GaAs. ACS Nano, 2013, 7, 3868-3875.	7.3	14
80	Observation of interface states by high-resolution electron-energy-loss spectroscopy in metal-GaAs(110) junctions. Physical Review B, 1996, 53, 12948-12955.	1.1	13
81	Hole pairing in high-T _c superconductors: Symmetry-driven configuration interaction mechanism. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1996, 18, 89-103.	0.4	13
82	The evolution of self-assembled InAs/GaAs(001) quantum dots grown by growth-interrupted molecular beam epitaxy. Nanotechnology, 2008, 19, 505701.	1.3	13
83	Pair interaction between Ge islands on vicinal Si(001) surfaces. Physical Review B, 2010, 81, .	1.1	13
84	Valence band density of states and X-ray photoelectron spectrum of GaS. Canadian Journal of Physics, 1978, 56, 700-703.	0.4	12
85	Cluster approach to the three-band Hubbard model of the Cu-O plane: Superconducting pairs. Physical Review B, 1997, 56, 14711-14716.	1.1	12
86	$d_{x^2-y^2}$ pairing in Cu-O clusters and in the plane. European Physical Journal B, 1999, 10, 293-304.	0.6	12
87	The GaAs(100)-(4 \times 4) surface: a new perspective from energy loss spectra. Surface Science, 2003, 524, L71-L76.	0.8	12
88	Electronic properties of laser-deposited Bi ₂ Sr ₂ CaCu ₂ O _{8-δ} thin films by X-ray photoemission and X-ray auger spectroscopies. Physica C: Superconductivity and Its Applications, 1989, 159, 447-460.	0.6	11
89	Canonical transformation of the three-band Hubbard model and hole pairing. Solid State Communications, 1998, 109, 229-233.	0.9	11
90	Valence band and In-4d core level photoemission study of de-capped and ion-bombarded-annealed InAs(001) epitaxial surfaces. Surface Science, 2005, 576, 123-130.	0.8	11

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91	Palladium clusters on graphite: A Bremsstrahlung Isochromat Spectroscopy study. Solid State Communications, 1990, 73, 251-255.	0.9	10
92	X-ray-photoemission-spectroscopy study of the surface deterioration of Bi ₂ Sr ₂ CaCu ₂ O ₈ and Bi _{1.7} Pb _{0.3} Sr ₂ CaCu ₂ O ₈ single crystals at 26 K. Physical Review B, 1991, 43, 11500-11503.	1.1	10
93	Symmetry-induced correlation effects and hole pairing in the Cu ₅ O ₄ model cluster. Solid State Communications, 1997, 101, 671-676.	0.9	10
94	In situ X-ray absorption measurements of the Cu/MgO() interface. Surface Science, 2002, 512, L341-L345.	0.8	10
95	Single quantum dot emission by nanoscale selective growth of InAs on GaAs: A bottom-up approach. Applied Physics Letters, 2008, 93, 231904.	1.5	10
96	Coarsening effect on island-size scaling: The model case InAs/GaAs(001). Physical Review E, 2012, 86, 061605.	0.8	10
97	Far ultraviolet absorption spectrum of the K ⁺ ion in KCl. Solid State Communications, 1974, 15, 1431-1434.	0.9	9
98	Reactivity of the Bi ₂ Sr ₂ CaCu ₂ O ₈ and Bi _{1.7} Pb _{0.3} Sr ₂ CaCu ₂ O ₈ surfaces for d-metal overlayers. Physica C: Superconductivity and Its Applications, 1992, 196, 79-89.	0.6	9
99	Anisotropy of the GaAs(001)- $\sqrt{2}\times\sqrt{2}$ surface from high-resolution electron energy loss spectroscopy. Physical Review B, 2003, 67, .	1.1	9
100	Folding and stacking defects of graphene flakes probed by electron nanobeam. Applied Physics Letters, 2011, 99, .	1.5	9
101	Determination of the optical constants of the Si ₃ N ₄ -SiO ₂ system by the method of the angular modulation of reflectance. Surface Science, 1974, 45, 227-237.	0.8	8
102	Wave-length-modulated absorption of InSe above the fundamental edge. Lettere Al Nuovo Cimento Rivista Internazionale Della Societ� Italiana Di Fisica, 1978, 21, 49-53.	0.4	8
103	EXAFS and XANES studies of local order in oxide glasses: Manganese impurity defects and vanadium low symmetry complexes. Journal of Non-Crystalline Solids, 1987, 94, 336-344.	1.5	8
104	Dynamic behavior of silver islands growing on GaAs(001) $\sqrt{2}\times\sqrt{2}$ substrate. Surface Science, 2000, 445, L17-L22.	0.8	8
105	In _x Ga(1-x)As quantum dots grown on GaAs studied by EXAFS in total reflection mode (RefLEXAFS). Nuclear Instruments & Methods in Physics Research B, 2003, 200, 85-89.	0.6	8
106	Driving Ge Island Ordering on Nanostructured Si surfaces. Nanoscience and Nanotechnology Letters, 2011, 3, 841-849.	0.4	8
107	New method for determining the optical constants by the angular modulation of reflectance. Surface Science, 1973, 37, 994-1001.	0.8	7
108	X-ray photoemission spectrum of the III-VI layer compound GaTe in the region of the valence bands. Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics, 1981, 105, 59-64.	0.9	7

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109	Two-hole quasiparticles and pairing in the Hubbard model of high- superconducting cuprates. Journal of Physics Condensed Matter, 1996, 8, L265-L269.	0.7	7
110	Formation and ordering of Ge nanocrystals on SiO ₂ using FIB nanolithography. Materials Science in Semiconductor Processing, 2006, 9, 812-816.	1.9	7
111	Adsorption of molecular oxygen on GaAs(001) studied using high-resolution electron energy-loss spectroscopy. Physical Review B, 2006, 73, .	1.1	7
112	Study of the fast-states structure at the surface of n-type germanium. Nuovo Cimento, 1962, 26, 1205-1220.	1.0	6
113	Measurement of the spectral distribution of the Frascati electron synchrotron radiation in the (80Å-1200) Å... region. Lettere Al Nuovo Cimento Rivista Internazionale Della Società Italiana Di Fisica, 1970, 3, 15-18.	0.4	6
114	Influence of the hydrogenation on the electrical resistance of palladium thin films. Physica Status Solidi A, 1977, 42, K41-K45.	1.7	6
115	Thermoreflectance studies of yttrium-iron garnet crystals. Journal of Physics C: Solid State Physics, 1979, 12, 5233-5243.	1.5	6
116	Interface formation between d metals and the Bi ₂ Sr ₂ CaCu ₂ O ₈ surface. Physica C: Superconductivity and Its Applications, 1991, 180, 101-107.	0.6	6
117	Pairing in the Hubbard model: the Cu O cluster versus the Cu-O plane. European Physical Journal B, 2000, 14, 269-280.	0.6	6
118	Comparative study of low temperature growth of InAs and InMnAs quantum dots. Nanotechnology, 2011, 22, 195602.	1.3	6
119	Ordering of Ge islands on Si(001) substrates patterned by nanoindentation. Thin Solid Films, 2011, 519, 4207-4211.	0.8	6
120	The role of kinetics on the Mn-induced reconstructions of the GaAs(001) surface. Journal of Applied Physics, 2011, 109, .	1.1	6
121	Hug-like island growth of Ge on strained vicinal Si(111) surfaces. Applied Physics Letters, 2011, 99, 161907.	1.5	6
122	Scaling behavior of GaAs and GaMnAs quantum rings grown by droplet epitaxy. Applied Physics Letters, 2012, 101, 141901.	1.5	6
123	Influence of an electric field on the exciton absorption in KBr. Physics Letters, 1966, 23, 405-406.	2.2	5
124	The local structure of random ternary alloys by EXAFS. Progress in Crystal Growth and Characterization, 1984, 10, 55-63.	0.8	5
125	Microscopic aspects of the Fe/Bi ₂ Sr ₂ CaCu ₂ O ₈ reactive interface. Physical Review B, 1994, 49, 9103-9110.	1.1	5
126	Configuration interaction and pairing in superconducting cuprates. Nuovo Cimento Della Società Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1997, 19, 1329-1334.	0.4	5

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127	Comparative study of Ag growth on GaAs(001) and (110) surfaces. Surface Science, 1998, 419, 24-28.	0.8	5
128	W= 0 pairing in Hubbard and related models of low-dimensional superconductors. Journal of Physics Condensed Matter, 2004, 16, R1387-R1422.	0.7	5
129	A study of the pair distribution function of self-organized Ge quantum dots. Applied Physics Letters, 2008, 93, .	1.5	5
130	Etch pits and tunnel barrier in chemically etched YBa ₂ Cu ₃ O _{7-δ} crystals by scanning tunneling microscopy. Physica C: Superconductivity and Its Applications, 1992, 200, 251-256.	0.6	4
131	Electronic structure of the GaAs(001)2 \times 4 and GaAs(110) surfaces studied by high-resolution electron-energy-loss spectroscopy. Physical Review B, 1998, 58, R10139-R10142.	1.1	4
132	CANONICAL TRANSFORMATION OF THE HUBBARD MODEL AND W = 0 PAIRING: COMPARISON WITH EXACT DIAGONALIZATION RESULTS. International Journal of Modern Physics B, 2000, 14, 2994-2999.	1.0	4
133	Growth and Characterization of Ge Nanostructures on Si(111). Lecture Notes in Physics, 2002, , 252-262.	0.3	4
134	XPS and STM study of Mn incorporation on the GaAs(001) surface. Superlattices and Microstructures, 2009, 46, 258-265.	1.4	4
135	Fabrication of SiGe rings and holes on Si(001) by flash annealing. Applied Surface Science, 2013, 283, 813-819.	3.1	4
136	Beneficial defects: exploiting the intrinsic polishing-induced wafer roughness for the catalyst-free growth of Ge in-plane nanowires. Nanoscale Research Letters, 2014, 9, 358.	3.1	4
137	Irreversible order-disorder transformation of Ge(O α %O α %1) probed by scanning tunnelling microscopy. Journal of Physics Condensed Matter, 2015, 27, 435001.	0.7	4
138	On the influence of multiple reflections on the electroreflectance spectrum of the ground-exciton line of GaSe. Journal of Physics and Chemistry of Solids, 1976, 37, 733-736.	1.9	3
139	Reflectivity and thermally modulated reflectivity of yttrium, gadolinium, erbium and ytterbium iron garnets. Lettere Al Nuovo Cimento Rivista Internazionale Della Societ \grave{a} Italiana Di Fisica, 1980, 29, 537-544.	0.4	3
140	K and L X-ray thresholds in III α %VI layer semiconductors. Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics, 1981, 105, 25-29.	0.9	3
141	Correlation effects on theL3VV Auger line shape ofCd1 α %xMnxTe. Physical Review B, 1987, 36, 7428-7432.	1.1	3
142	Study of laser-deposited Bi ₂ Sr ₂ CaCu ₂ O ₈ + δ thin films by rutherford backscattering, X-ray photoemission and X-ray Auger spectroscopies. Journal of the Less Common Metals, 1989, 151, 13-21.	0.9	3
143	Self-assembling and Ordering of Ge/Si Quantum Dots on Flat and Nanostructured Surfaces. Materials Research Society Symposia Proceedings, 2001, 696, 1.	0.1	3
144	Self-assembly of Ge quantum dots on Silicon: An example of controlled nanomanufacturing. Superlattices and Microstructures, 2009, 46, 318-323.	1.4	3

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145	Morphological and Electronic Characterization of Functionalized Graphene Nanoribbons Obtained by the Unzipping of Single-Wall Carbon Nanotubes: A Scanning Tunneling Microscopy Study. Fullerenes Nanotubes and Carbon Nanostructures, 2013, 21, 302-310.	1.0	3
146	The InAs/GaAs(001) Quantum Dots Transition: Advances on Understanding. , 2008, , 1-23.		3
147	InAs Epitaxy on GaAs(001): A Model Case of Strain-Driven Self-assembling of Quantum Dots. , 2012, , 73-125.		3
148	Optical Properties in the High Energy Range. , 1986, , 289-397.		3
149	Shift of the exciton absorption induced by a strong electric field in alkali halides. Il Nuovo Cimento B, 1967, 51, 303-309.	0.1	2
150	Electroreflectance at Oblique Incidence in Ge. Physica Status Solidi (B): Basic Research, 1968, 28, K109.	0.7	2
151	Many-body contribution to XPS line asymmetry in palladium-hydrogen systems. Societa Italiana Di Fisica Nuovo Cimento B-General Physics, Relativity Astronomy and Mathematical Physics and Methods, 1977, 39, 720-726.	0.2	2
152	Towards a Controlled Growth of Self-assembled Nanostructures: Shaping, Ordering, and Localization in Ge/Si Heteroepitaxy. , 2012, , 201-263.		2
153	Effects of substrate vicinality on 3D islanding in Ge/Si epitaxy. Thin Solid Films, 2013, 543, 88-93.	0.8	2
154	Semiconductor Quantum Dots: Model Case Ge/Si. , 0, , 863-912.		2
155	Electronic structure of the Ge/Si(1 \times 0 \times 5) hetero-interface: an ARPES and DFT study. Journal of Physics Condensed Matter, 2018, 30, 465502.	0.7	2
156	Electric field effects on indirect optical transitions in AgCl. Journal of Physics C: Solid State Physics, 1970, 3, 2200-2203.	1.5	1
157	Effects of anisotropy on the electroreflectance spectra of GaSe at oblique incidence. Societa Italiana Di Fisica Nuovo Cimento B-General Physics, Relativity Astronomy and Mathematical Physics and Methods, 1977, 38, 176-184.	0.2	1
158	EELPS investigation of YBa ₂ Cu ₃ O _{7-δ} thin films and sintered samples. Physica C: Superconductivity and Its Applications, 1991, 180, 132-135.	0.6	1
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